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# Multi-disciplinary Simulation for 2.5D/3DIC Co-Design

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3DIC CPS Multiphysics



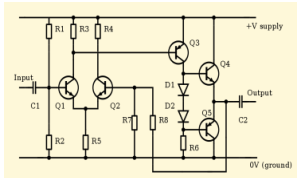
# Evolution of Chip Design Complexity

Multiphysics signoff is a MUST for silicon success

**1980**

1-2 $\mu$

Transistor-level

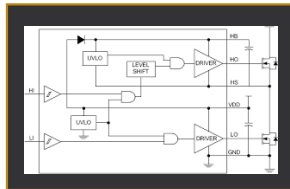


Functional

**1990**

Sub-micron

Gate-level



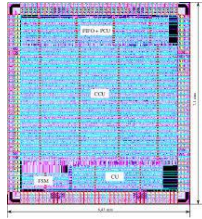
Functional

Timing

**2000**

Deep submicron

ASIC



Functional

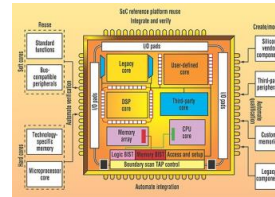
Timing

Power

**2010**

Nanometer

System on Chip



Functional

Timing

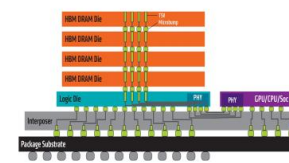
Power

Reliability

**2015**

Sub 100nm

Stacked Die



Functional

Timing

Power

Reliability

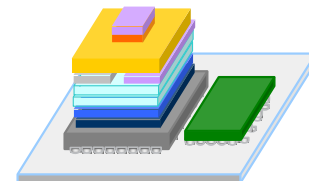
Thermal

EMI

**2020**

5/3 nm

Complex 3DIC



Functional

Timing

Power

Reliability

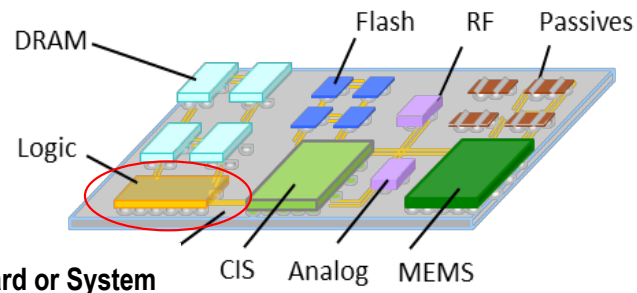
Thermal

EMI

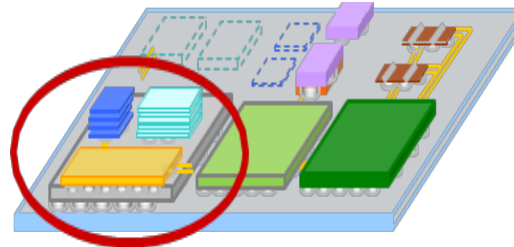
Mechanical

References: Various, Applied Materials, Intel, AMD, Google images

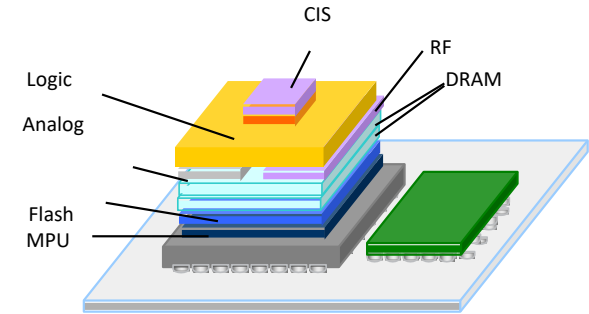
# Single Die vs. Multi Dies



Single die with Own Package in Conventional 2D System



System in Package: Multi Dies in Single Package




Courtesy of TSMC Reference Flow

- Each die can be a noise source of other dies
  - Chip or package only analysis brings inaccurate/optimistic result
  - Multi-die aware package level power integrity and signal integrity
  - Package aware multi-die concurrent power integrity
- Package level reliability (Electromigration, Joule heating) becomes more important
- Thermal and thermal induced stress analysis for heat accumulation and thermal coupling by multi-dies



# Challenges in 2.5D Stacking & Analysis Needs

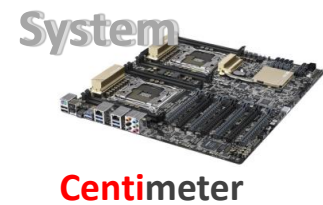
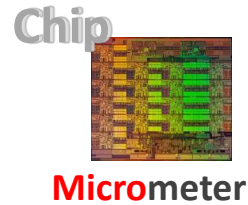
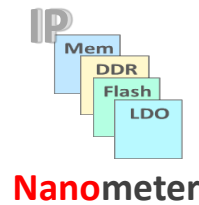
Characteristic	Interposer Materials				Physics based analysis enabled by 
	Ideal Properties	Glass	Silicon	Organic	
Electrical	<ul style="list-style-type: none"> <li>High Resistivity</li> <li>Low Loss</li> </ul>	Green	Red	Green	2.5D Stacked Die Analysis <b>PI , SI , EM Workflows</b>
Thermal	<ul style="list-style-type: none"> <li>High Conductivity</li> <li>CTE matched to Si</li> </ul>	Yellow	Green	Red	2.5D Stacked Die Analysis <b>TI Workflow</b>
Mechanical	<ul style="list-style-type: none"> <li>High Strength</li> <li>High Modulus</li> </ul>	Green	Yellow	Red	2.5D Stacked Die Analysis <b>Mechanical Analysis Workflow</b>
Physical	<ul style="list-style-type: none"> <li>Smooth Surface Finish</li> <li>Large area availability</li> <li>Ultra thin</li> </ul>	Green	Yellow	Yellow	2.5D Stacked Die Analysis <b>Structural Analysis Workflow</b>
Chemical	<ul style="list-style-type: none"> <li>Resistance to process chemicals</li> </ul>	Green	Yellow	Yellow	
Processability	<ul style="list-style-type: none"> <li>Ease of via formation</li> </ul>	Red	Yellow	Yellow	
Cost	<ul style="list-style-type: none"> <li>Low cost per I/O at 25um pitch</li> </ul>	Green	Red	Red	

Source: Phil Marcoux , [www.allvia.com](http://www.allvia.com)

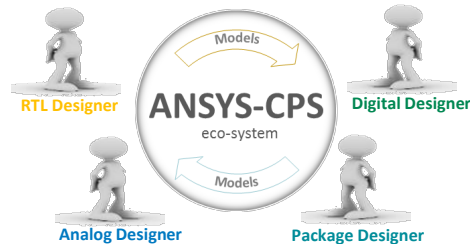
# ANSYS Multiphysics Simulations for Electronics Systems

## Core Technologies

### Multiscale Solvers



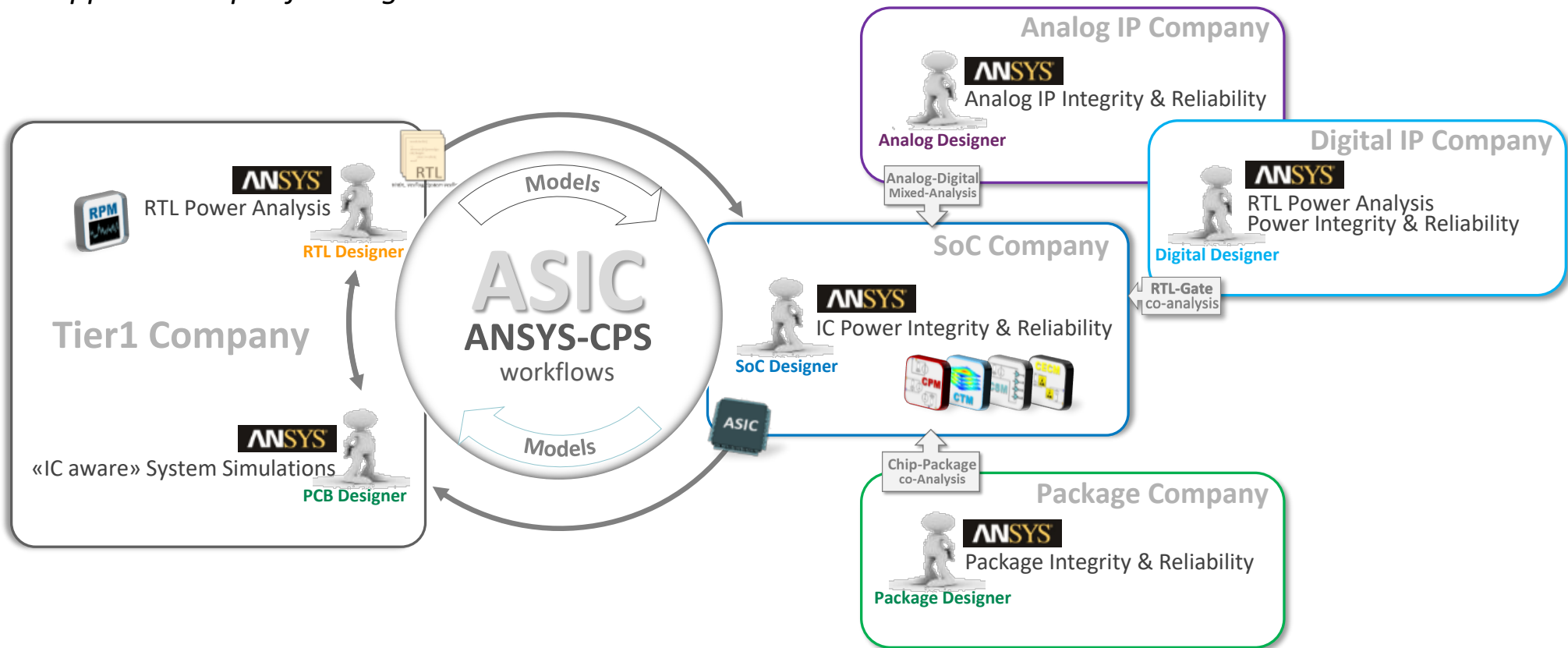
### Multiphysics Models



- ✓ **Cell Models** – APL
- ✓ **IP Models** – Custom Macro Model
- ✓ **RTL Models** – RTL Power Model
- ✓ **SoC Models** – Power, Signal, Thermal, ESD
- ✓ **Package Models** – Chip Package co-Analysis

# Reality of Electronics Market Ecosystem

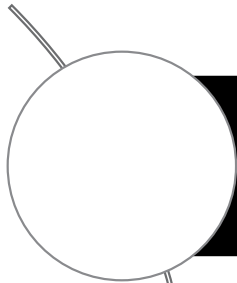
Application Specific Integrated Circuit Use Case



CPS: Chip Package System CPM: Chip Power Model CTM: Chip Thermal Model CSM: Chip Signal Model CECM: Chip ESD Compact Model RPM: RTL Power Model CPA: Chip Package Analysis CMM: Custom Macro Model

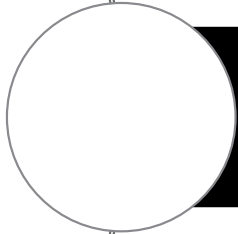


# Ansys Multiphysics solutions for 2.5D/3DIC design



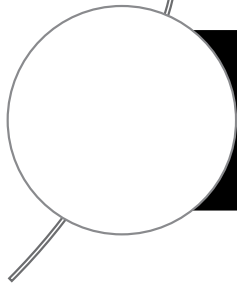
## Power Integrity

- Full PDN Power Integrity Signoff for Complex 2.5D/3DIC analysis



## ElectroThermal/Mechanical Integrity

- Full ElectroThermal/Mechanical Integrity Sign off for Complex 2.5D/3DIC analysis

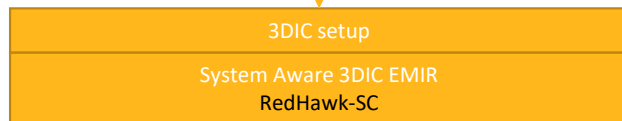
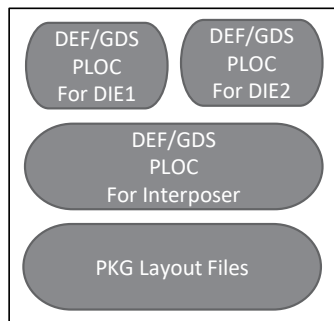


## Power Induced Signal Integrity

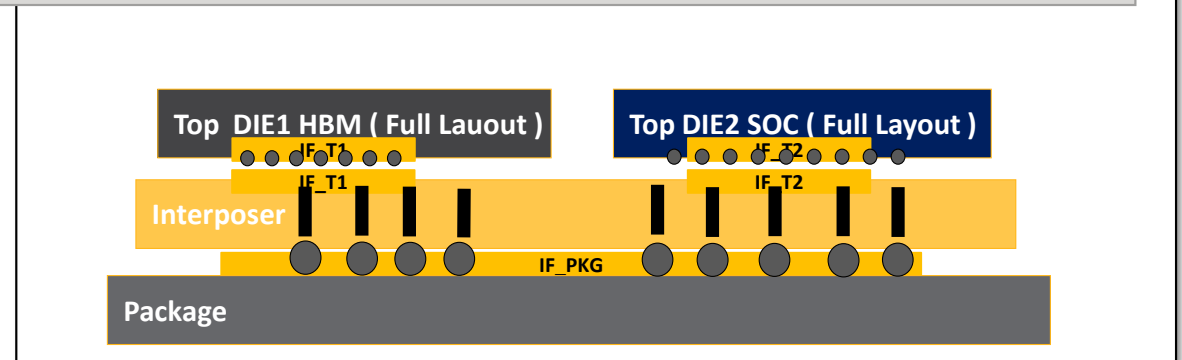
- Chip Package System aware Power induced Signal Analysis for High Capacity HBM 3DIC structure

# System Aware 3DIC Chip Level PI analysis Flow

*concurrent analysis*



- Shared P/G network in multiple dies, interposers, PKG, and Board
- Need simultaneous full detailed and model-based analysis with coupled noise propagation



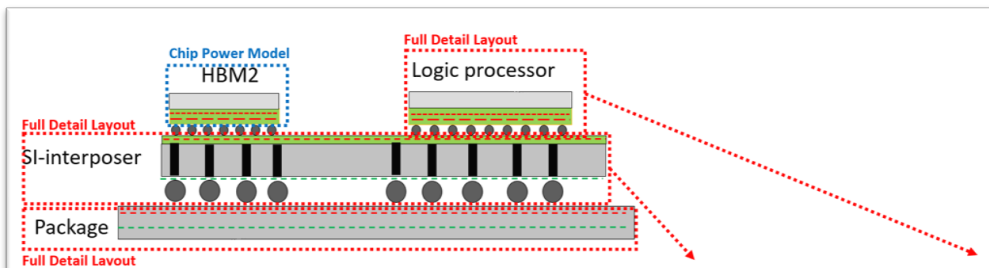
**Example Design Structure :**  
*HBM MEMORY ( Full Detail Layout ) +  
Logic Processor ( Full detail Layout ) +  
Interposer ( Full detail Layout ) +  
Package ( Full detail Layout )*

**Typical Design Size :**  
*Multi-Billion Node Counts  
Total Bump Count : > 100K  
Runtime : ~ 5Hrs*

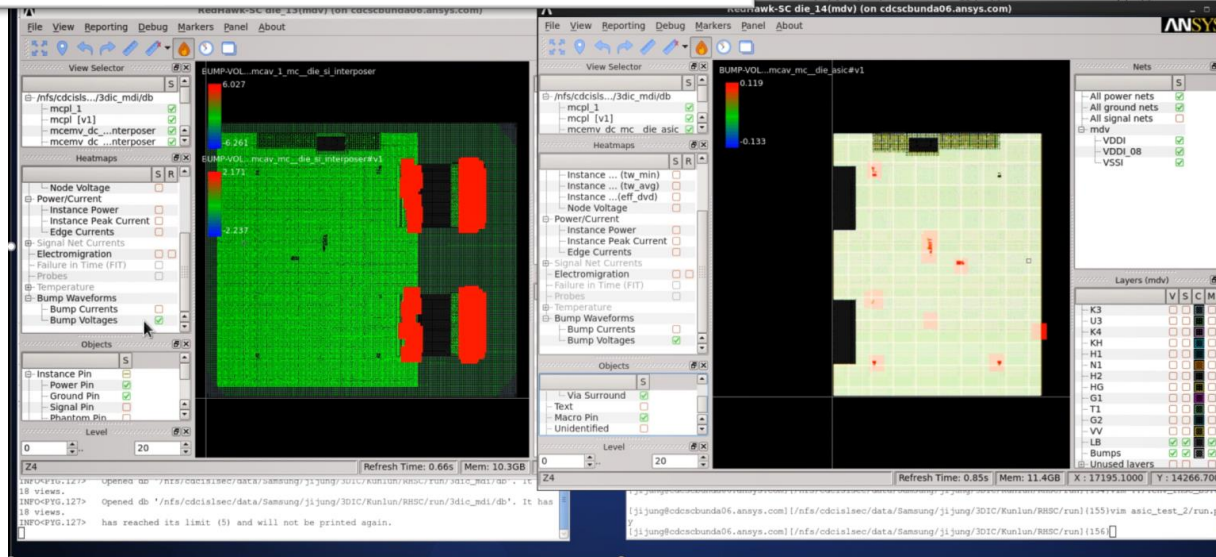


# 2.5D/3DIC RedHawk-SC onchip power integrity maps

Full die and Interposer reports are in one session, 900mm<sup>2</sup> interposer size



Multiple Scenarios  
Built on Big Data System



**Design Structure :**  
**HBM2E ( Chip Power Model ) +**  
**Logic Processor +**  
**Interposer +**  
**Package**

**Design Size :**  
**30mm x 30mm ( Interposer size )**  
**50mm x 50mm ( Package size )**

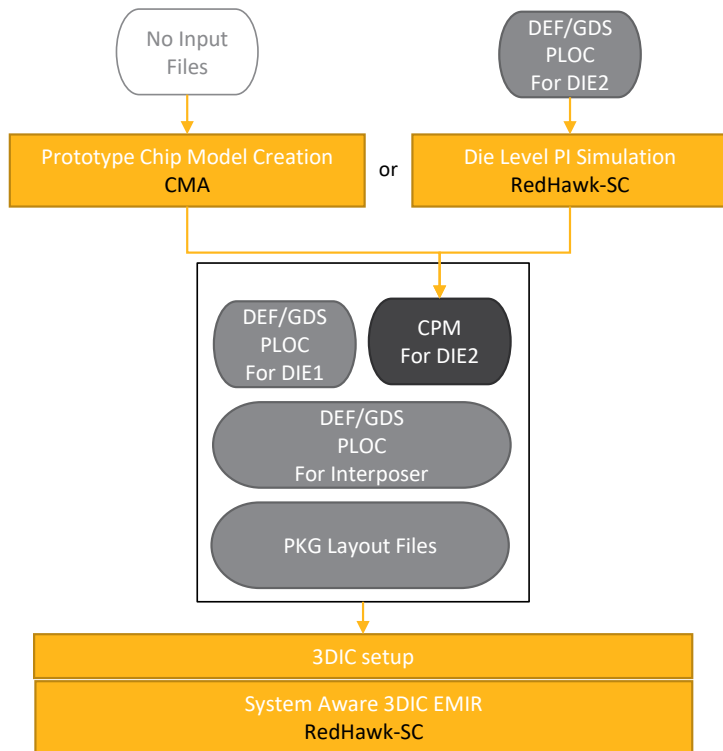
**Total Node Count :**  
**Over 5Billion**

**Total Bump Count :**  
**Over 200K**

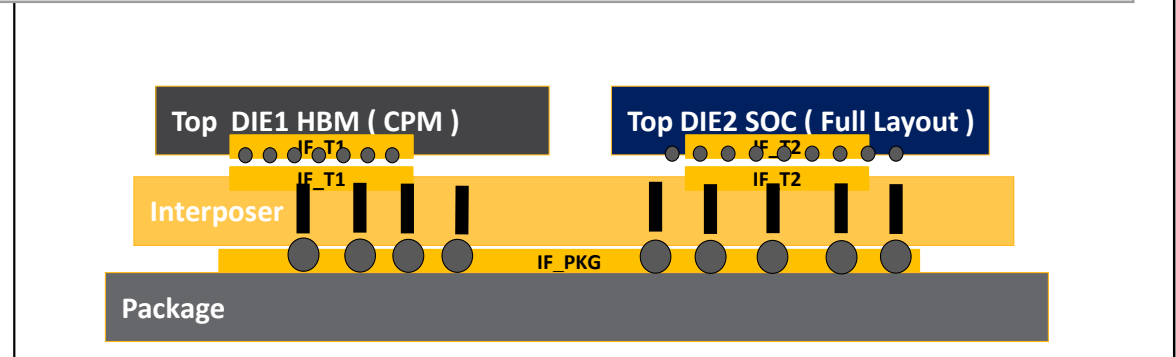


# System Aware 3DIC Chip Level PI analysis Flow

*model based mixed with concurrent analysis*



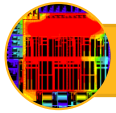
- Shared P/G network in multiple dies, interposers, PKG, and Board
- Need simultaneous full detailed and model-based analysis with coupled noise propagation



**Example Design Structure :**  
***HBM MEMORY ( CPM from CMA ) +***  
***Logic Processor ( Full detail Layout ) +***  
***Interposer ( Full detail Layout ) +***  
***Package ( Full detail Layout )***

**Typical Design Size :**  
***Multi-Billion Node Counts***  
***Total Bump Count : > 100K***  
***Runtime : ~ 5Hrs***

# How Ansys Delivers The Required Capabilities



## Power Integrity

### Engineering Challenges

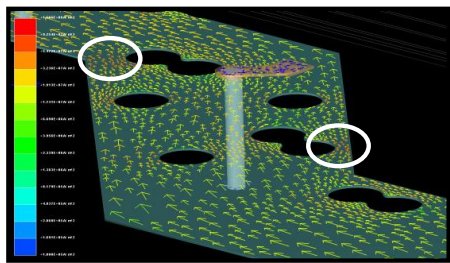
- Improve power efficiency
- Verify **Power Delivery Network**
- Power planes and Decoupling
- Meet emission compliance targets
- Minimize Electromigration

### Ansys Capabilities

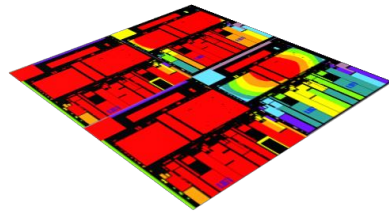
- Signoff PDN from Transistor to system
- 2D/2.5D/3DIC support
- Chip aware system co-analysis
- System aware chip co-analysis
- Multiscale modeling : **Chip Power Model**, **Custom Macro Model**, **Chip Model Analyzer**

### Example Outputs

- Transient Power noise
- Current signature
- Voltage drop
- Impedance Profile
- Optimized Decoupling schemes
- Power/Ground Plane Resonance
- Electrical Model



Current crowding

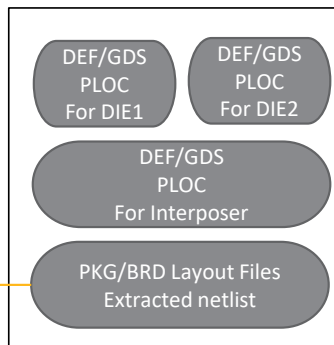


Voltage drop at IC level



Power supply noise vs time

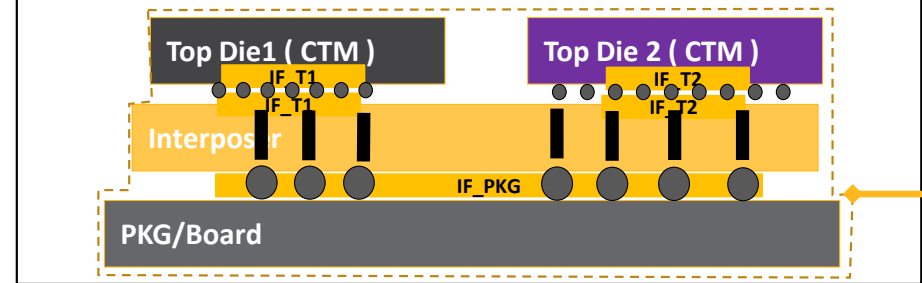
# Ansys Chip Package System ElectroThermal/Mechanical Flow



3DIC On Chip Multiphysics Analysis

3DIC Multiphysics Analysis  
RedHawk-SC

- Thermal issue is critical in 3DIC design
- Joule heating at interface is critical
- Static/Transient both needed



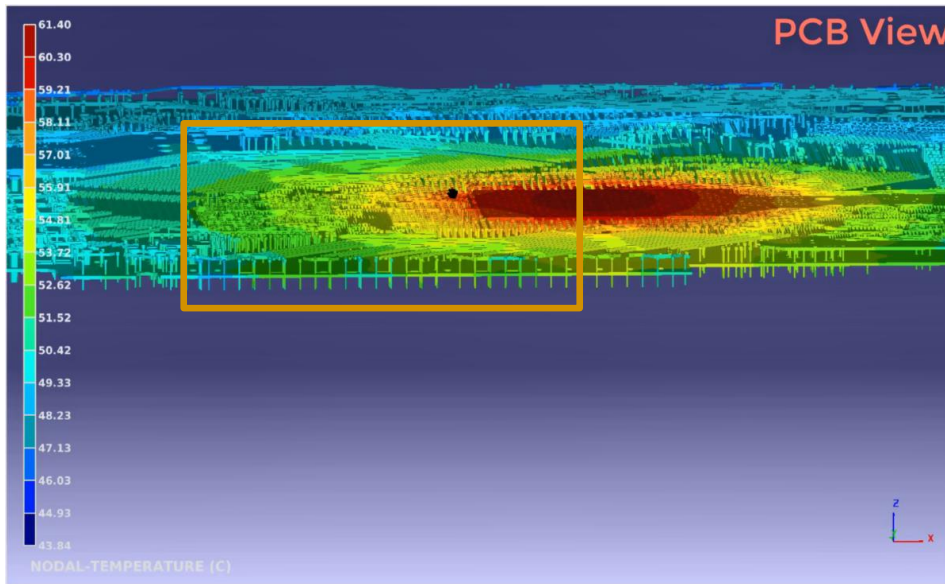
**Design Structure :**  
**Logic Processor ( CTM ) +**  
**Interposer ( CTM ) +**  
**PKG/Board ( Layout )**

**Concurrent ElectroThermal**  
**analysis :**  
**Coupling inside of 3DIC Structure**  
**ElectroThermal/Mechanical**

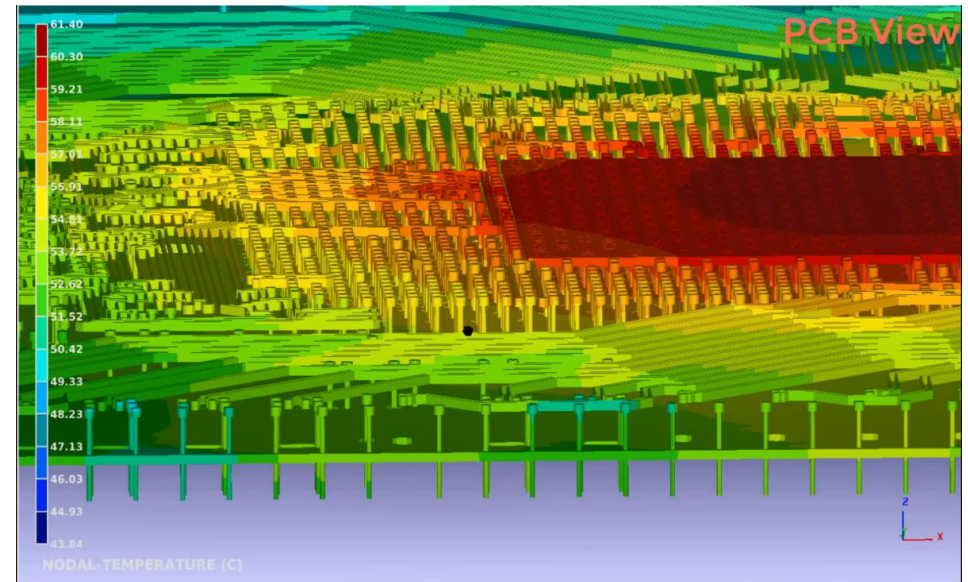
**Boundary condition at the**  
**surface of the structure**

# RedHawk-SC ElectroThermal Analysis Result

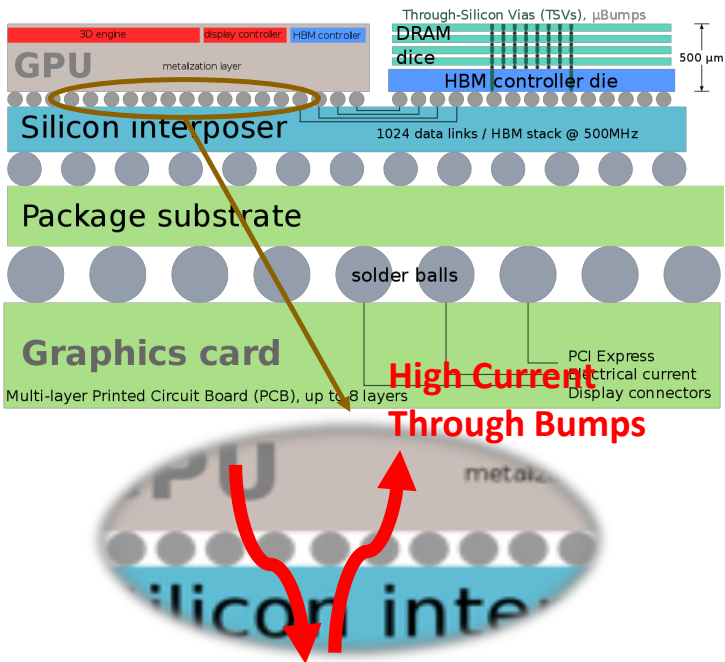
*Full 3DIC detailed Temperature Profile Maps*



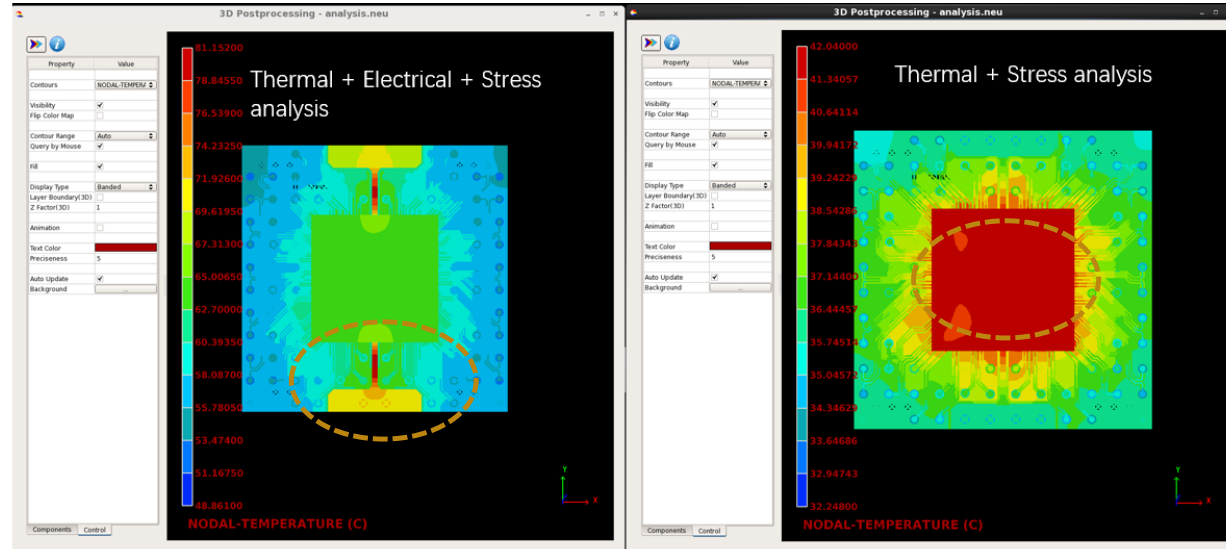
Zoomed area



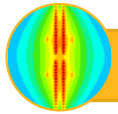
# ElectroThermal co-analysis



Power-hungry HPC design encounters ElectroThermal issue due to interaction of thermal cycling and current on micro bumps and solder balls. Ansys Solution catches this ElectroThermal issue considering **Joule heating effect**



# How Ansys Delivers The Required Capabilities



## Thermal/Mechanical Integrity

### Engineering Challenges

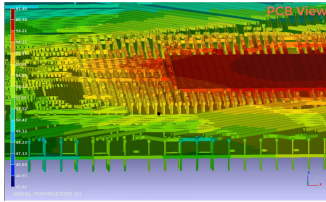
- FinFET Thermal Effects
- Joules heating
- Power dissipation
- Thermal runaway
- Thermal-induced stress

### Ansys Capabilities

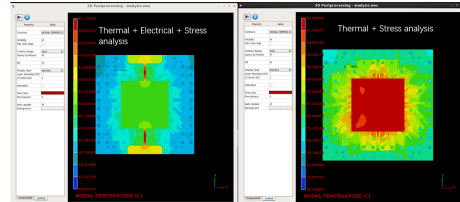
- Chip level Self heat analysis
- Chip-aware system thermal analysis
- System aware chip thermal analysis
- CFD based thermal solver
- **Chip Thermal Model**
- Prototyping with early power estimation

### Example Outputs

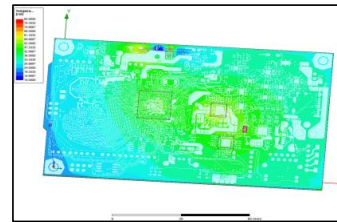
- Heat map
- Temperature Contours
- Velocity Vectors
- Stress, deformation



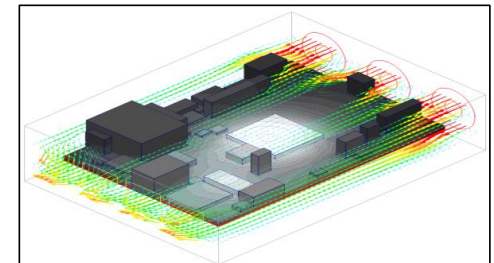
Full detailed Thermal for Chip Package PCB



ElectroThermal with Joule heating with bump current



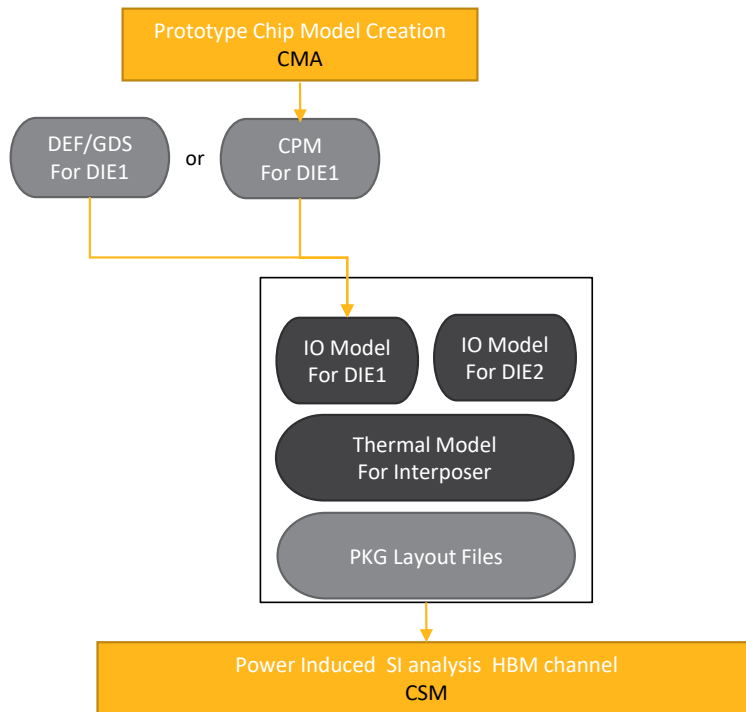
Joule Heating with DC current



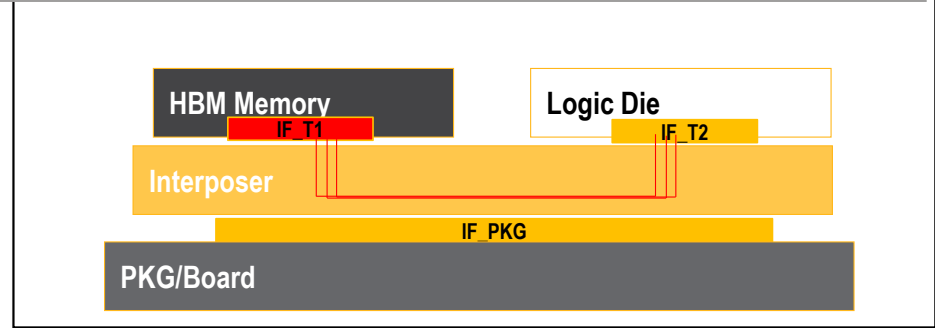
Full System Level CFD thermal solver with air flow

# Chip Package System aware PSI Analysis for High capacity HBM

Prototyping and signoff



- Shared P/G network in multiple dies, interposers, PKG, and Board
- HBM is sensitive to power noise to signal
- HBM channel complexity increases for performance need
- HBM vendors reluctant to provide full layouts



**Design Structure :**  
**HBM ( CIOM + CPM ) +**  
**Interposer ( Extracted Model ) +**  
**PKG + Board ( Extracted Model )**

*Simultaneous Switching impact to Signal Integrity in HBM signal lines*  
*Virtual Compliance kit for very easy reporting*  
*CPM editing for what if of PI noise insertion in case there is no full layout given from HBM vendors*



# 2.5D/3DIC CSM Signal Integrity

## Power induced Signal Integrity analysis

### JEDEC reports

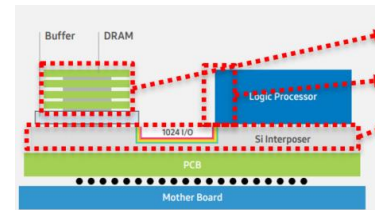
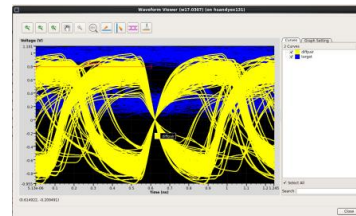
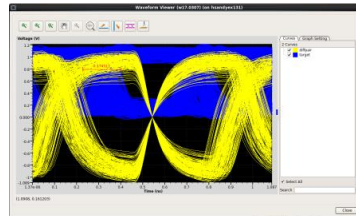
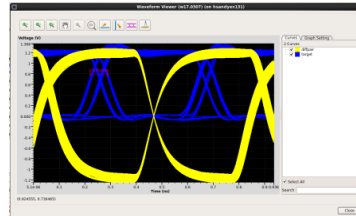
SelfDelay	Waveform Timing	Eyediagram Timing	Noise	Jitter Period	Jitter Clock	Jitter Trigger	
Target	Reference	Vref(V)	Start Time(ns)	End Time(ns)	Period jitter(ns)	Pass/Fail	
1	✓ DQa0/PAD	WDQSa0/PADP	0.792	10	200	0.0715096	N/A
2	✓ DQa1/PAD	WDQSa0/PADP	0.792	10	200	0.0720017	N/A
3	✓ DQa2/PAD	WDQSa0/PADP	0.792	10	200	0.0709741	N/A
4	✓ DQa3/PAD	WDQSa0/PADP	0.792	10	200	0.0715371	N/A
5	✓ DQa4/PAD	WDQSa0/PADP	0.792	10	200	0.0728677	N/A
6	✓ DQa5/PAD	WDQSa0/PADP	0.792	10	200	0.0710761	N/A
7	✓ DQa6/PAD	WDQSa0/PADP	0.792	10	200	0.072928	N/A
8	✓ DQa7/PAD	WDQSa0/PADP	0.792	10	200	0.0700145	N/A

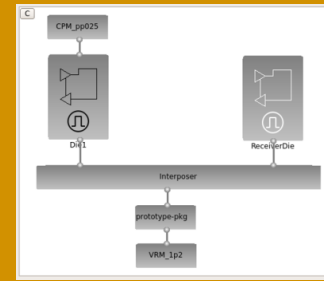
SelfDelay	Waveform Timing	Eyediagram Timing	Noise	Jitter Period	Jitter Clock	Jitter Trigger	
Target	Reference	Vref(V)	Start Time(ns)	End Time(ns)	Period jitter(ns)	Pass/Fail	
1	✓ DQa0/PAD	WDQSa0/PADP	0.792	10	200	0.174517	N/A
2	✓ DQa1/PAD	WDQSa0/PADP	0.792	10	200	0.174671	N/A
3	✓ DQa2/PAD	WDQSa0/PADP	0.792	10	200	0.174613	N/A
4	✓ DQa3/PAD	WDQSa0/PADP	0.792	10	200	0.174773	N/A
5	✓ DQa4/PAD	WDQSa0/PADP	0.792	10	200	0.17461	N/A
6	✓ DQa5/PAD	WDQSa0/PADP	0.792	10	200	0.174908	N/A
7	✓ DQa6/PAD	WDQSa0/PADP	0.792	10	200	0.174614	N/A
8	✓ DQa7/PAD	WDQSa0/PADP	0.792	10	200	0.174919	N/A

SelfDelay	Waveform Timing	Eyediagram Timing	Noise	Jitter Period	Jitter Clock	Jitter Trigger	
Target	Reference	Vref(V)	Start Time(ns)	End Time(ns)	Period jitter(ns)	Pass/Fail	
1	✓ DQa0/PAD	WDQSa0/PADP	0.792	20	150	0.605613	N/A
2	✓ DQa1/PAD	WDQSa0/PADP	0.792	20	150	0.600637	N/A
3	✓ DQa2/PAD	WDQSa0/PADP	0.792	20	150	0.604458	N/A
4	✓ DQa3/PAD	WDQSa0/PADP	0.792	20	150	0.602089	N/A
5	✓ DQa4/PAD	WDQSa0/PADP	0.792	20	150	0.597891	N/A
6	✓ DQa5/PAD	WDQSa0/PADP	0.792	20	150	0.602697	N/A
7	✓ DQa6/PAD	WDQSa0/PADP	0.792	20	150	0.597195	N/A
8	✓ DQa7/PAD	WDQSa0/PADP	0.792	20	150	0.604444	N/A

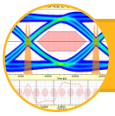


CMA generates CPM with power noise connecting to a Channel Model in CSM for Signal Integrity Analysis



**Design Structure :**  
**HBM2E ( Chip Power Model ) +**  
**Logic Processor +**  
**Interposer +**  
**Package**  
**Design Size :**  
**30mm x 30mm ( Interposer size )**  
**50mm x 50mm ( Package size )**  
**Total Node Count :**  
**Over 5Billion**  
**Total Bump Count :**  
**Over 200K**

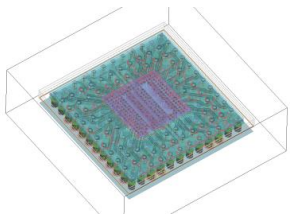
# How Ansys Delivers The Required Capabilities



## Signal Integrity

### Engineering Challenges

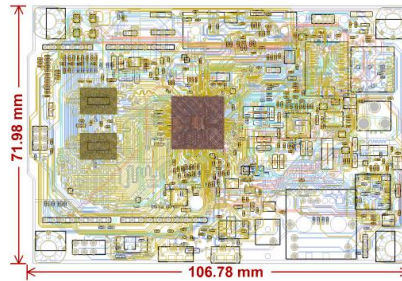
- Assess performance of multi-gigabit SERDES & DDRx Memory
- Minimize Crosstalk
- Meet standards requirements
- Achieve interface bandwidth



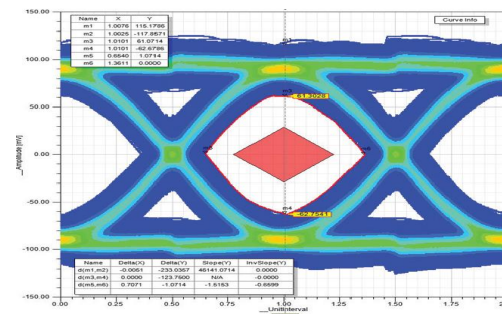
Multilayer BGA Package layout

### Ansys Capabilities

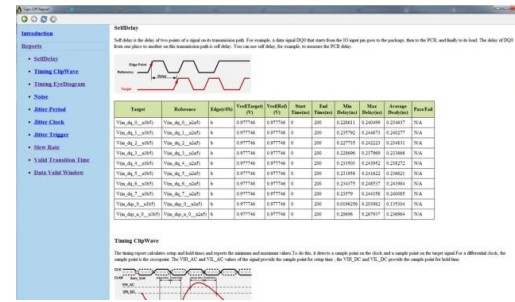
- 3D Full wave & Hybrid EM Solvers
- IBIS/IBIS AMI Generation
- Power aware SI sign-off using Chip Signal Model
- Virtual Compliance Toolkits



Multilayer PCB layout



Eye diagram of a SERDES link



DDR Virtual Compliance sign-off report



Thank You

